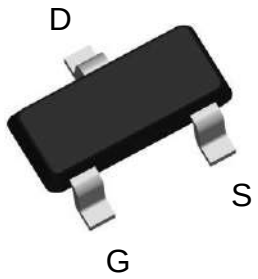
P-Channel Enhancement Mode MOSFET

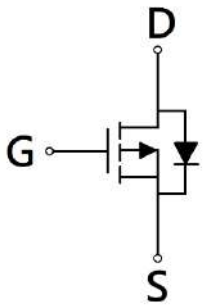
Features:

- Advanced trench process technology
- High density cell design for ultra low on resistance
- Excellent thermal and electrical capabilities
- Compact and low profile SOT-23 package

SOT-23



BV_{DSS}	-20V
I_D@V_{GS}=-4.5V, T_A=25°C	-2.8A
$R_{DS(ON)}$ typ.@V_{GS}=-4.5V, I_D=-2.8A	77mΩ
$R_{DS(ON)}$ typ.@V_{GS}=-2.5V, I_D=-2A	108mΩ



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KWP2301	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (T_A=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	
Continuous Drain Current @ V_{GS}=-4.5V, T_A=25°C	*a	I_D	-2.8	A
Continuous Drain Current @ V_{GS}=-4.5V, T_A=70°C	*a		-2.2	
Pulsed Drain Current	*b	I_{DM}	-10.8	
Continuous Body Diode Forward Current @ T_A=25°C	*a	I_S	-0.9	
Avalanche Current @ L=0.1mH		I_{AS}	-9	
Avalanche Energy @ L=0.5mH		E_{AS}	6.3	mJ
Total Power Dissipation	T_A=25°C *a	P_D	1.1	W
	T_A=70°C *a		0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	°C

Thermal Data

Parameter		Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	*a	$R_{\theta JA}$	112	°C/W

Note:

*a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR -4 board with 2 oz. copper, in a still air environment with T_A=25℃. The power dissipation P_D is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

*b. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃. Ratings are based on low frequency and low duty cycles to keep initial T_J=25℃.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	-20	-	-	V	V_{GS}=0V, I_D=-250μA
$V_{GS(th)}$	-0.45	-	-1.2		V_{DS}=V_{GS}, I_D=-250μA
G_{FS}	-	7	-	S	V_{DS}=-5V, I_D=-3A
I_{GSS}	-	-	±100	nA	V_{GS}=±8V, V_{DS}=0V
I_{DSS}	-	-	-1	μA	V_{DS}=-16V, V_{GS}=0V
$R_{DS(ON)}$	-	77	100	mΩ	V_{GS}=-4.5V, I_D=-2.8A
	-	108	150		V_{GS}=-2.5V, I_D=-2A
Dynamic					
Ciss	-	600	-	pF	V_{DS}=-10V, V_{GS}=0V, f=1MHz
Coss	-	60	-		
Crss	-	50	-		
Rg	-	14	-	Ω	f=1MHz
Qg *1, 2	-	8	-	nC	V_{DS}=-10V, I_D=-2A, V_{GS}=-4.5V
Qgs *1, 2	-	1	-		
Qgd *1, 2	-	1.7	-		
$t_{d(ON)}$ *1, 2	-	4	-	ns	V_{DS}=-10V, I_D=-2.8A, V_{GS}=-4.5V, R_{GS}=1Ω
tr *1, 2	-	20	-		
$t_{d(OFF)}$ *1, 2	-	50	-		
t_f *1, 2	-	5	-		
Source-Drain Diode					
V_{SD} *1	-	-0.86	-1.2	V	I_S=-1.6A, V_{GS}=0V
trr	-	6	-	ns	I_F=-1.6A, dI_F/dt=100A/μs
Qrr	-	1.7	-	nC	

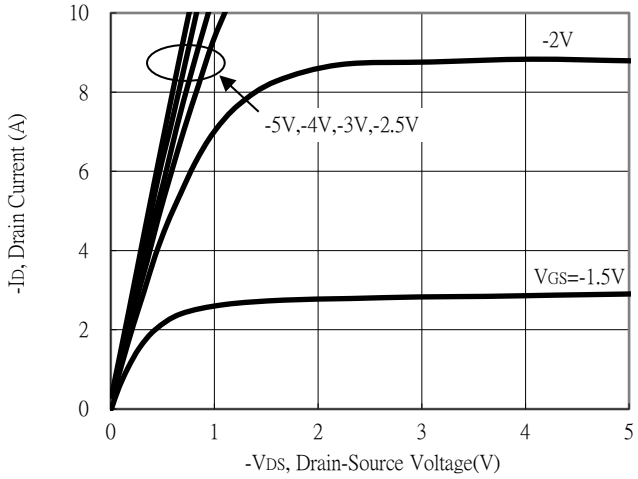
Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

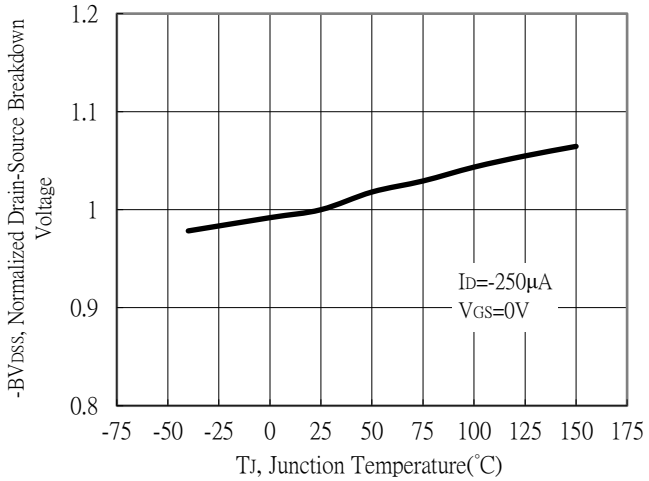
*2. Independent of operating temperature

Typical Characteristics

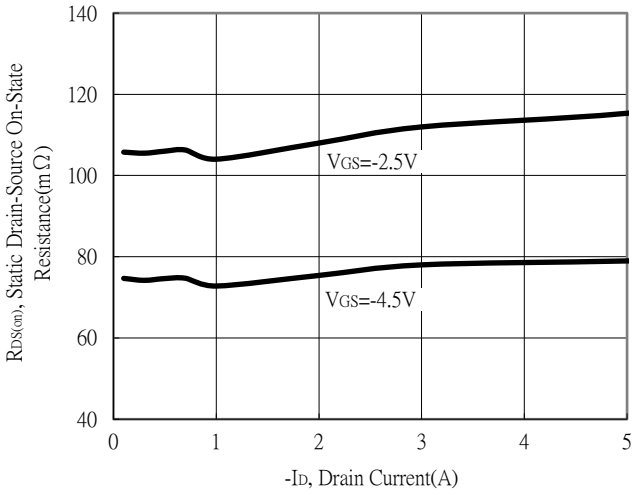
Typical Output Characteristics



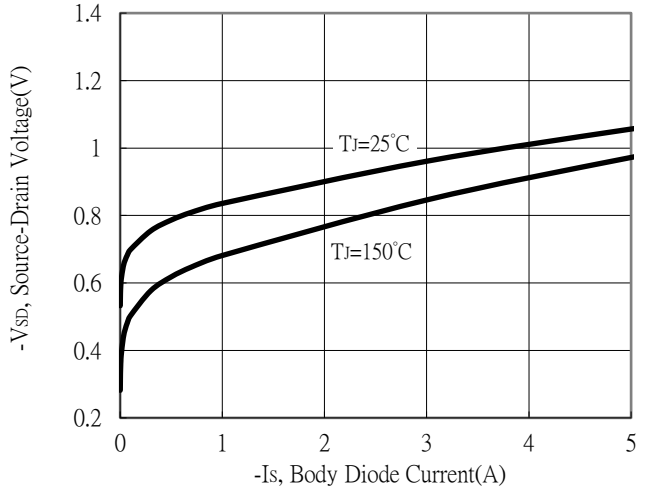
Breakdown Voltage vs Ambient Temperature



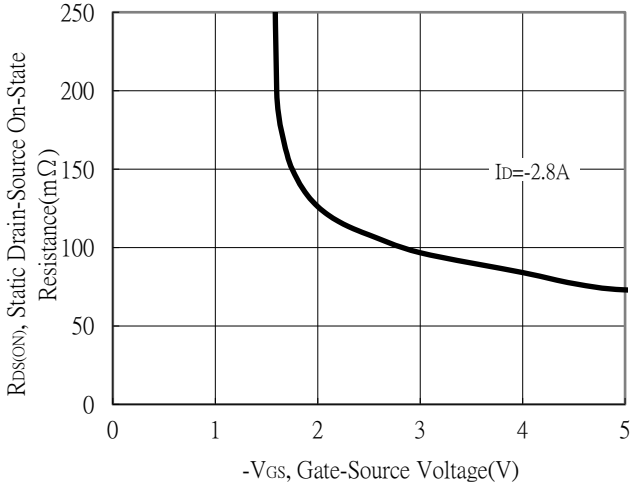
Static Drain-Source On-State resistance vs Drain Current



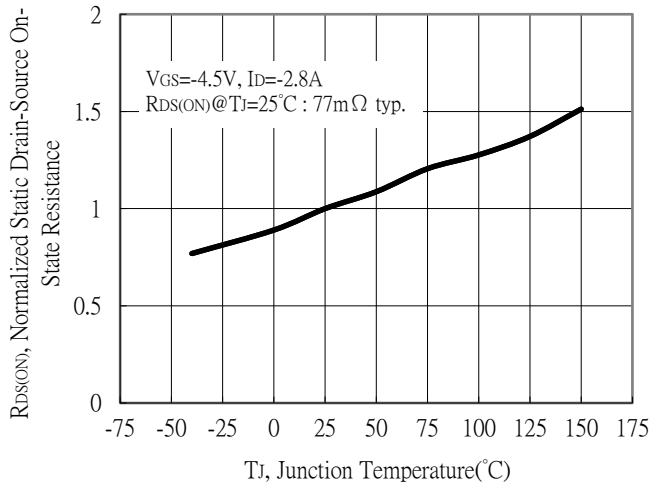
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

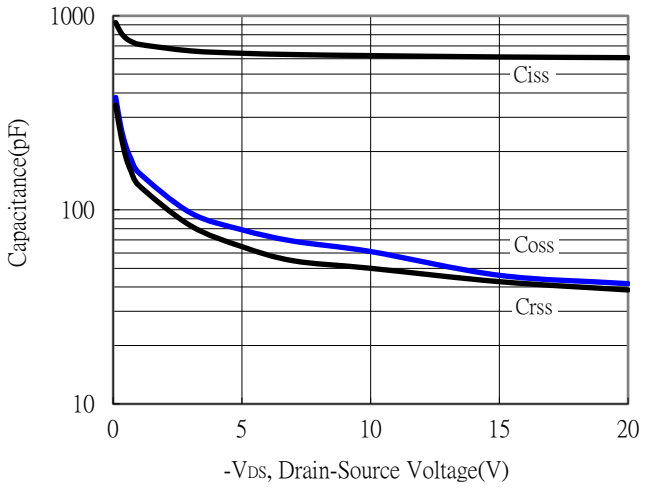


Drain-Source On-State Resistance vs Junction Temperature

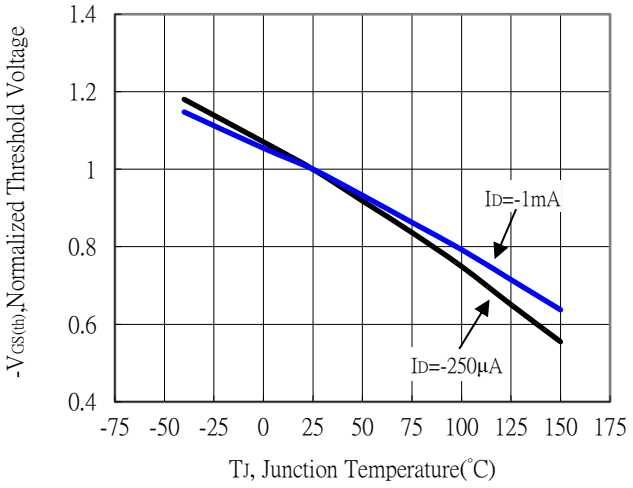


Typical Characteristics (Cont.)

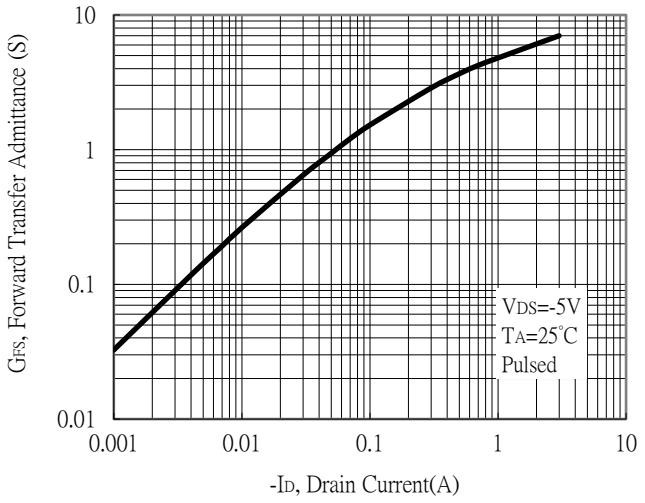
Capacitance vs Drain-to-Source Voltage



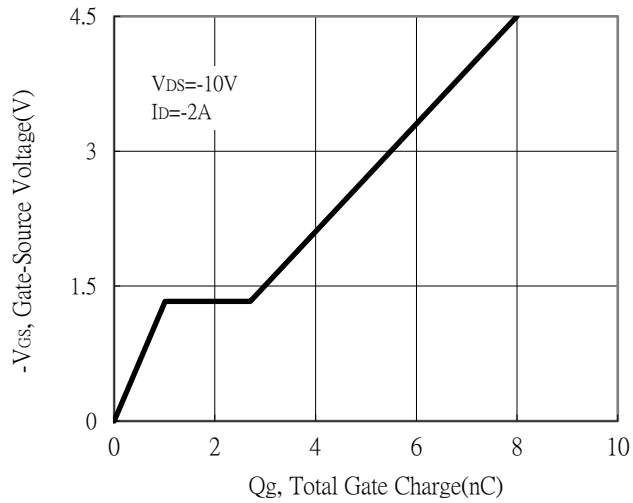
Threshold Voltage vs Junction Temperature



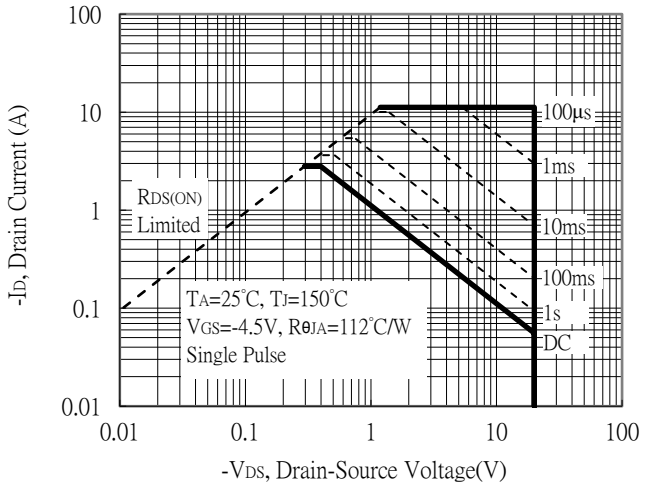
Forward Transfer Admittance vs Drain Current



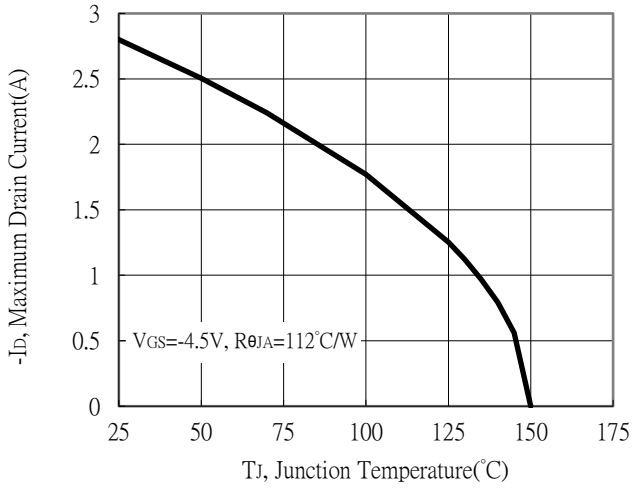
Gate Charge Characteristics



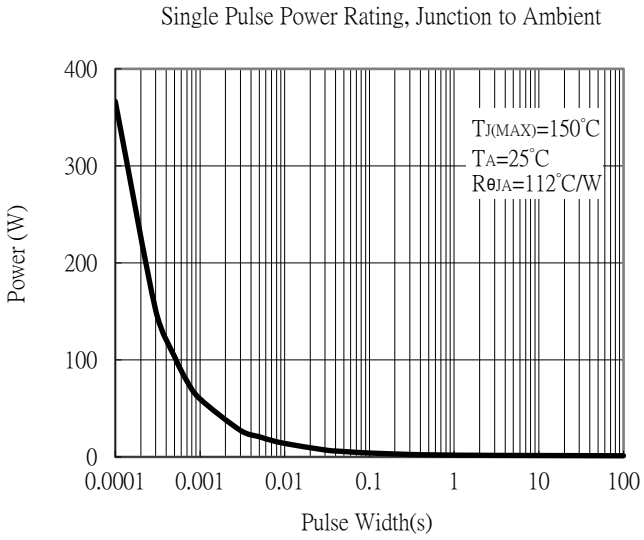
Maximum Safe Operating Area

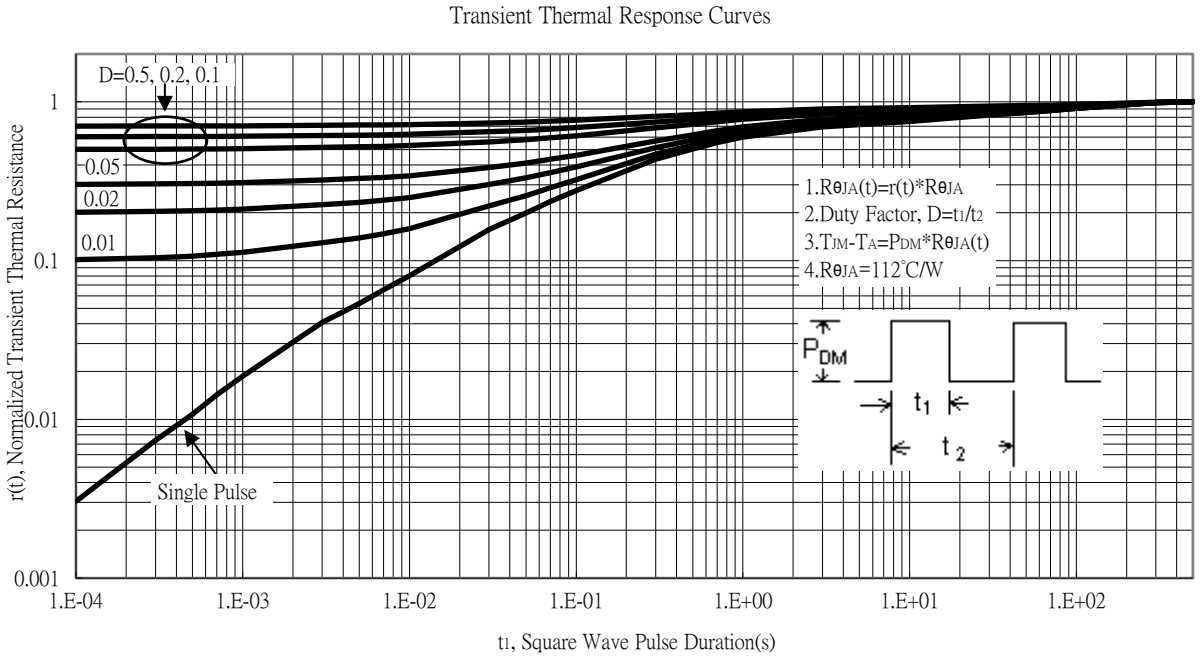


Maximum Drain Current vs JunctionTemperature

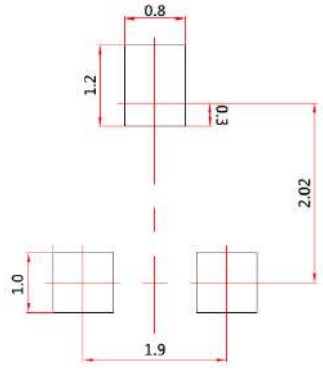


Typical Characteristics (Cont.)



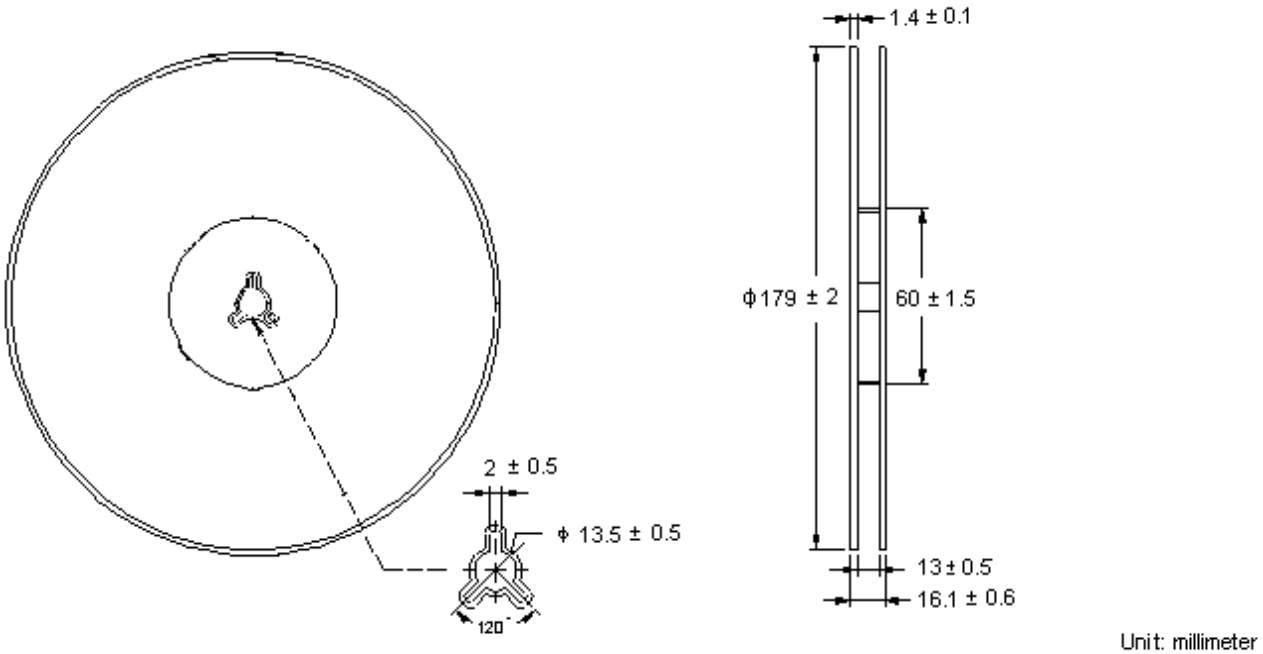


Recommended Soldering Footprint



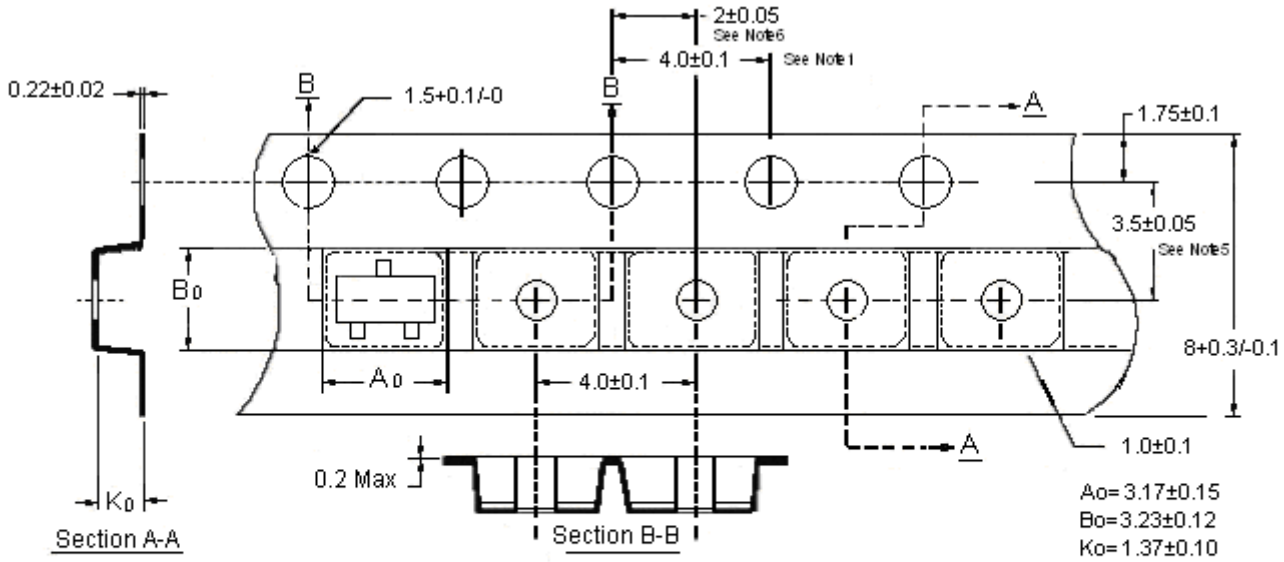
Unit : mm

Reel Dimension



Unit: millimeter

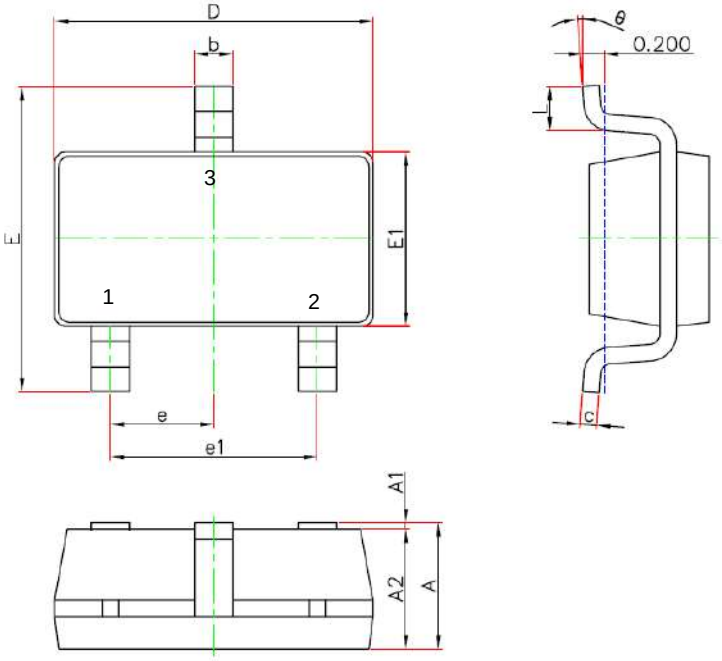
Carrier Tape Dimension



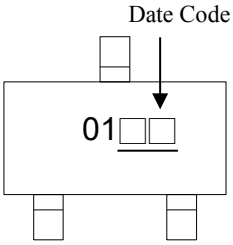
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

SOT-23 Dimension



Marking:



Style: Pin 1.Gate 2.Source 3.Drain

Date Code: Year+Month
Year: 3→2003, 4→2004
Month: 1→1, 2→2, • • •
9→9, A→10, B→11, C→12

3-Lead SOT-23 Plastic
Surface Mounted Package

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.035	0.049	0.90	1.25	E1	0.047	0.067	1.20	1.70
A1	0.000	0.004	0.00	0.10	E	0.089	0.116	2.25	2.95
A2	0.041	0.045	1.05	1.15	e	0.037 BSC		0.95 BSC	
b	0.012	0.020	0.30	0.50	e1	0.071	0.079	1.80	2.00
c	0.003	0.008	0.08	0.20	L	0.012	0.024	0.30	0.60
D	0.110	0.119	2.80	3.02	θ	0 °	8 °	0 °	8 °